FCI-InGaAs-XXX-WCER

High Speed InGaAs Photodiodes Mounted on Wraparound Ceramic

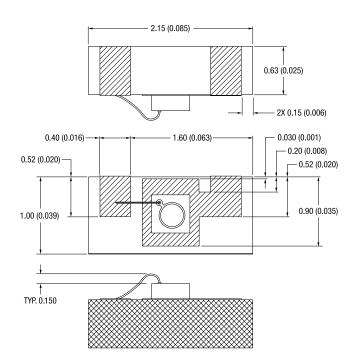
FCI-InGaAs-XXX-WCER with active area sizes of 75µm, 120µm, 300µm, 400µm and 500µm are part of a line of monitor photodiodes mounted on metallized ceramic substrates. These compact assemblies are designed for ease of integration. The chips can be epoxy or eutectic mounted onto the ceramic substrate.

APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitor
- Instrumentation

FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range
 900nm to 1700nm







Notes:

All units in millimeters (inches).
All devices are eutectic mounted with tolerance of ±50µm.

Absolute Maximum Ratings										
PARAMETERS	SYMBOL	MIN	МАХ	UNITS						
Storage Temperature	T _{stg}	-40	+85	°C						
Operating Temperature	T _{op}	0	+70	°C						
Soldering Temperature	T _{sld}		+260	°C						

Electro-Optical Characteristics T _A =23°C														23°C				
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-75WCER		FCI-InGaAs-120WCER		FCI-InGaAs-300WCER		FCI-InGaAs-400WCER			FCI-InGaAs-500WCEF						
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Active Area Diameter	AA_{ϕ}			75			120			300			400			500		μm
Responsivity	R _λ	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
		λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	Cj	$V_{R} = 5.0V$		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	Id	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_{R} = 5.0V,$ $R_{L} = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Reverse Voltage					20			20			15			15			15	v
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz